



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

2SB1308 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -3 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

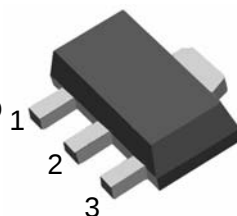
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$		-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.5	μA
DC current gain	$h_{FE} *$	$V_{CE}=-2V, I_C=-0.5A$	82	390	
Collector-emitter saturation voltage	$V_{CEsat} *$	$I_C=-1.5A, I_B=-0.15A$		-0.45	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-50mA$ $f=30MHz$	50		MHz

* Measured using pulse current.

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390

Marking	BFP,BFQ,BFR
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